AMENDMENTS TO THE CLAIMS:

Listing of claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1 - 15 (Canceled)

16. (Presently Amended) A method of manufacturing semiconductor light-emitting device comprising ~~the steps of~~:

growing a compound semiconductor epitaxial layer including an active layer on a substrate having a surface having an off-angle of 0.5 ° to 30 ° to a crystallographic plane of ~~low-degree surface orientation~~ (100), (111) or (0001);

forming a protective film having an opening on a surface of the compound semiconductor epitaxial layer; and

selectively growing a ridge-shaped compound semiconductor epitaxial layer to cover the opening.

17. (Original) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the compound semiconductor epitaxial layers including an active

layer further include a first conductivity type cladding layer and a second conductivity type first cladding layer.

18. (Original) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the ridge-shaped compound semiconductor epitaxial layer includes a second conductivity type second cladding layer.

19. (Original) The method for manufacturing semiconductor light-emitting device according to claim 18, wherein the second conductivity type second cladding layer is grown as to cover a portion of a surface of the protective film.

20. (New) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the crystallographic plane is (100) or (111).

21. (New) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the crystallographic plane is (0001).

22. (New) The method of manufacturing semiconductor light-emitting device according to claim 16, wherein the substrate has zinc-blende structure or a hexagonal system.

23. (New) A method of manufacturing semiconductor light-emitting device comprising:

growing a compound semiconductor epitaxial layer including an active layer and a cladding layer comprising material selected from the group consisting of AlGaAs, AlGaInAs, AlGaInP and AlGaInN on a substrate having a surface having an off-angle to a crystallographic plane of low-degree surface orientation;

forming a protective film having an opening on a surface of the compound semiconductor epitaxial layer; and

selectively growing a ridge shaped compound semiconductor epitaxial layer to cover the opening.